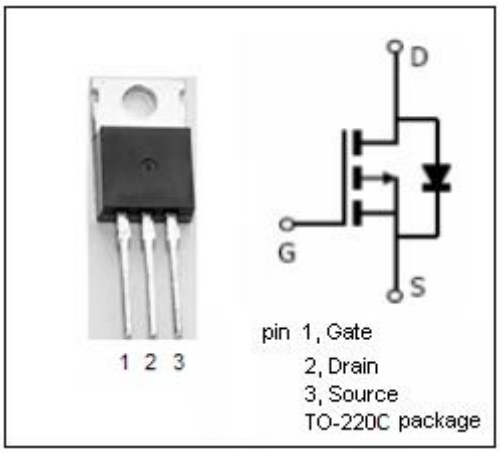
# isc P-Channel MOSFET Transistor ISCC1853




## • FEATURES

- Static drain-source on-resistance:
  $R_{DS(on)} \leqslant 40m\Omega$
- Enhancement mode
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## • DESCRIPTION

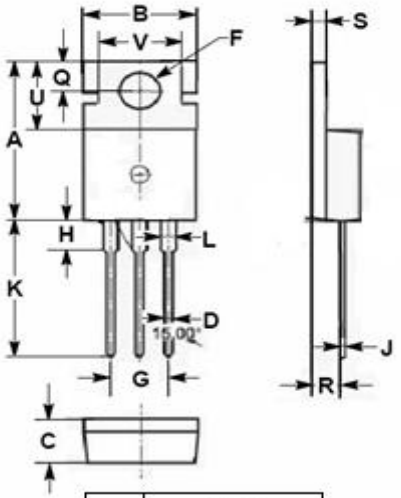
- Combine with the fast switching speed and ruggedized device design,provide the designer with an extremely efficient and reliable device for use in a wide variety of applications.

## • ABSOLUTE MAXIMUM RATINGS($T_a$=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | -60 | V |
| $V_{GS}$ | Gate-Source Voltage | ±20 | V |
| $I_D$ | Drain Current-Continuous | -24 | A |
| $I_{DM}$ | Drain Current-Single Pulsed | -60 | A |
| $P_D$ | Total Dissipation @$T_C$=25℃ | 43 | W |
| $T_j$ | Max. Operating Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature | -55~150 | ℃ |

## • THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---|---|---|---|
| Rth(j-c) | Channel-to-case thermal resistance | 2.9 | ℃/W |
| Rth(j-a) | Channel-to-ambient thermal resistance | 62 | ℃/W |




| DIM | mm MIN | MAX |
|---|---|---|
| A | 15.50 | 15.90 |
| B | 9.90 | 10.20 |
| C | 4.20 | 4.50 |
| D | 0.70 | 0.90 |
| F | 3.40 | 3.70 |
| G | 4.98 | 5.18 |
| H | 2.68 | 2.90 |
| J | 0.44 | 0.60 |
| K | 13.00 | 13.40 |
| L | 1.10 | 1.45 |
| Q | 2.70 | 2.90 |
| R | 2.30 | 2.70 |
| S | 1.29 | 1.35 |
| U | 6.45 | 6.65 |
| V | 8.66 | 8.86 |



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## ELECTRICAL CHARACTERISTICS

**$T_C$=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$=0V; $I_D$= -250 μA | -60 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$; $I_D$= -250 μA | -1.2 | | -2.4 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | $V_{GS}$= -10V; $I_D$= -20A | | | 40 | mΩ |
| $I_{GSS}$ | Gate-Source Leakage Current | $V_{GS}$= ±20V | | | ±100 | nA |
| $I_{DSS}$ | Drain-Source Leakage Current | $V_{DS}$= -60V; $V_{GS}$= 0V | | | -1 | μA |
| $V_{SD}$ | Diode forward voltage | Is= -1A; $V_{GS}$ = 0V | | | -1 | V |



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